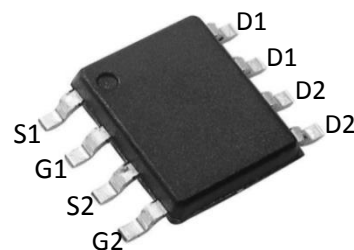


Description:

This Dual P-Channel MOSFET uses advanced trench technology and

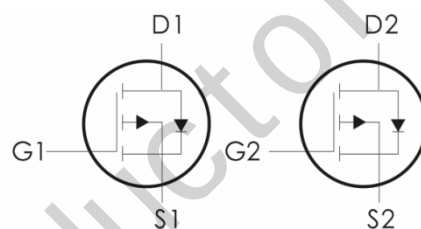
design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.



Features:

- 1) $V_{DS}=-30V, I_D=-7A, R_{DS(on)}<20m\Omega$ @ $V_{GS}=-10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra $R_{DS(on)}$.
- 5) Excellent package for good heat dissipation.



Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current- $T_C=25^\circ C$	-7	A
	Continuous Drain Current- $T_C=100^\circ C$	-5.1	
	Pulsed Drain Current ¹	-32	
E_{AS}	Single Pulse Avalanche Energy	---	mJ
P_D	Power Dissipation($T_C=25^\circ C$)	2.1	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	---	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	60	

Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourtce Breakdown Voltage	V _{GS} =0V, I _D =-250 μ A	-30	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V , V _{GS} =0V , T _J =25 °C	---	---	-1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =-250 μ A	-1.0	-1.6	-2.5	V
R _{DS(ON)}	Drain-Source On Resistance ²	V _{GS} =-10V, I _D =-8A	---	16.5	20	m Ω
		V _{GS} =-4.5V, I _D =-5A	---	25.6	32	
G _{FS}	Forward Transconductance	V _{DS} =-10V, I _D =-3A	---	6.8	---	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	1250	1820	pF
C _{oss}	Output Capacitance		---	160	235	
C _{rss}	Reverse Transfer Capacitance		---	90	130	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time ^{2,3}	V _{DD} =-15V , V _{GS} =-10V , R _G =6, I _D =-1A	---	5.8	11	ns
t _r	Rise Time ^{2,3}		---	18.8	36	ns
t _{d(off)}	Turn-Off Delay Time ^{2,3}		---	46.9	89	ns
t _f	Fall Time ^{2,3}		---	12.3	23	ns
Q _g	Total Gate Charge ^{2,3}	V _{DS} =-15V , V _G S=-4.5V , I _D =-5A	---	11	17	nC
Q _{gs}	Gate-Source Charge ^{2,3}		---	3.4	6	nC
Q _{gd}	Gate-Drain “Miller” Charge ^{2,3}		---	4.2	8	nC
Drain-Source Diode Characteristics						
V _{SD}	Source-Drain Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A	---	---	-1	V

Notes:

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\cong 300\mu s$, duty cycle $\cong 2\%$.
3. Essentially independent of operating temperature.

Typical Characteristics: ($T_C=25^\circ\text{C}$ unless otherwise noted)

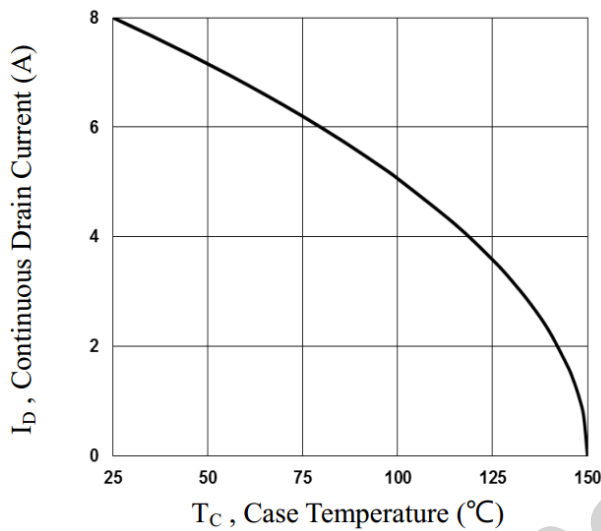


Fig.1 Continuous Drain Current vs. T_C

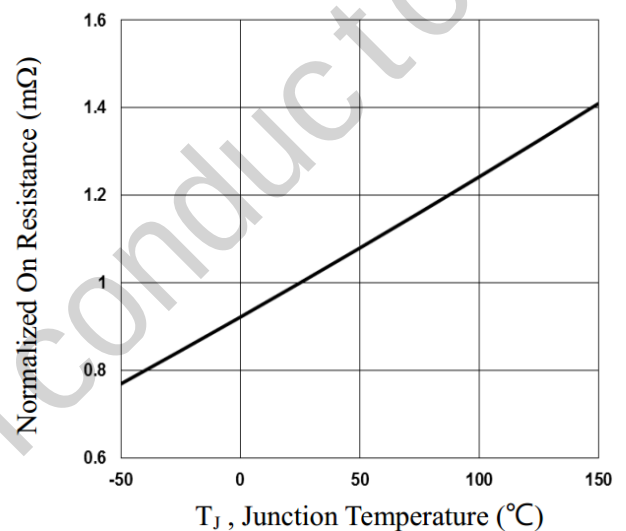


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

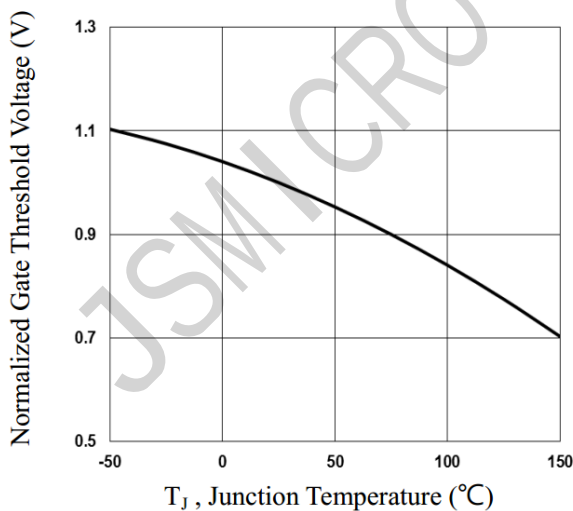


Fig.3 Normalized V_{th} vs. T_J

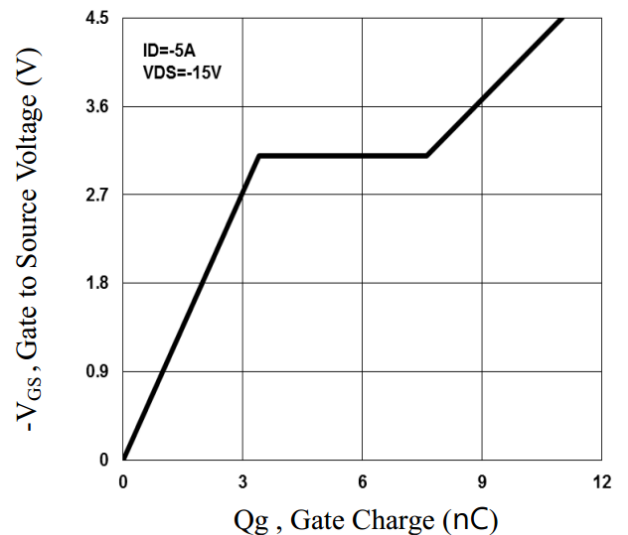


Fig.4 Gate Charge Waveform

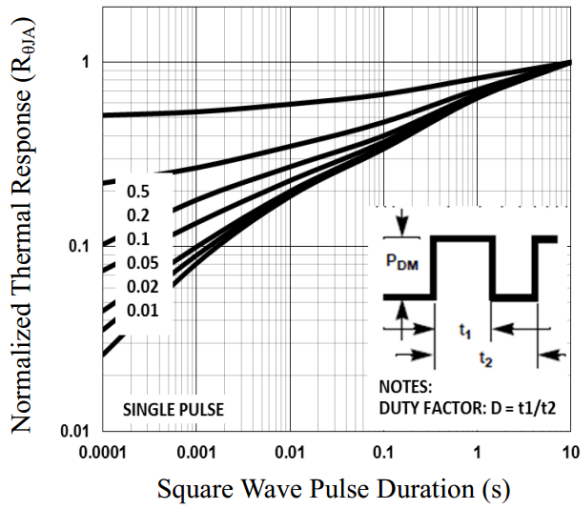


Fig.5 Normalized Transient Impedance

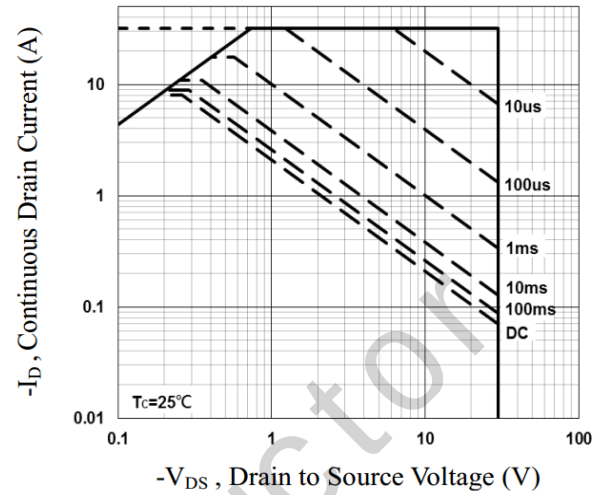


Fig.6 Maximum Safe Operation Area

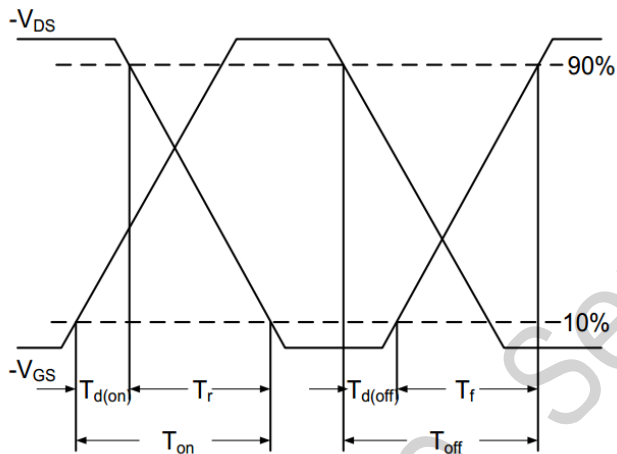


Fig.7 Switching Time Waveform

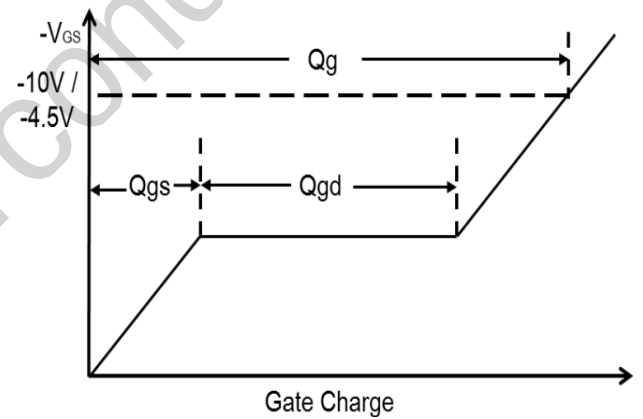
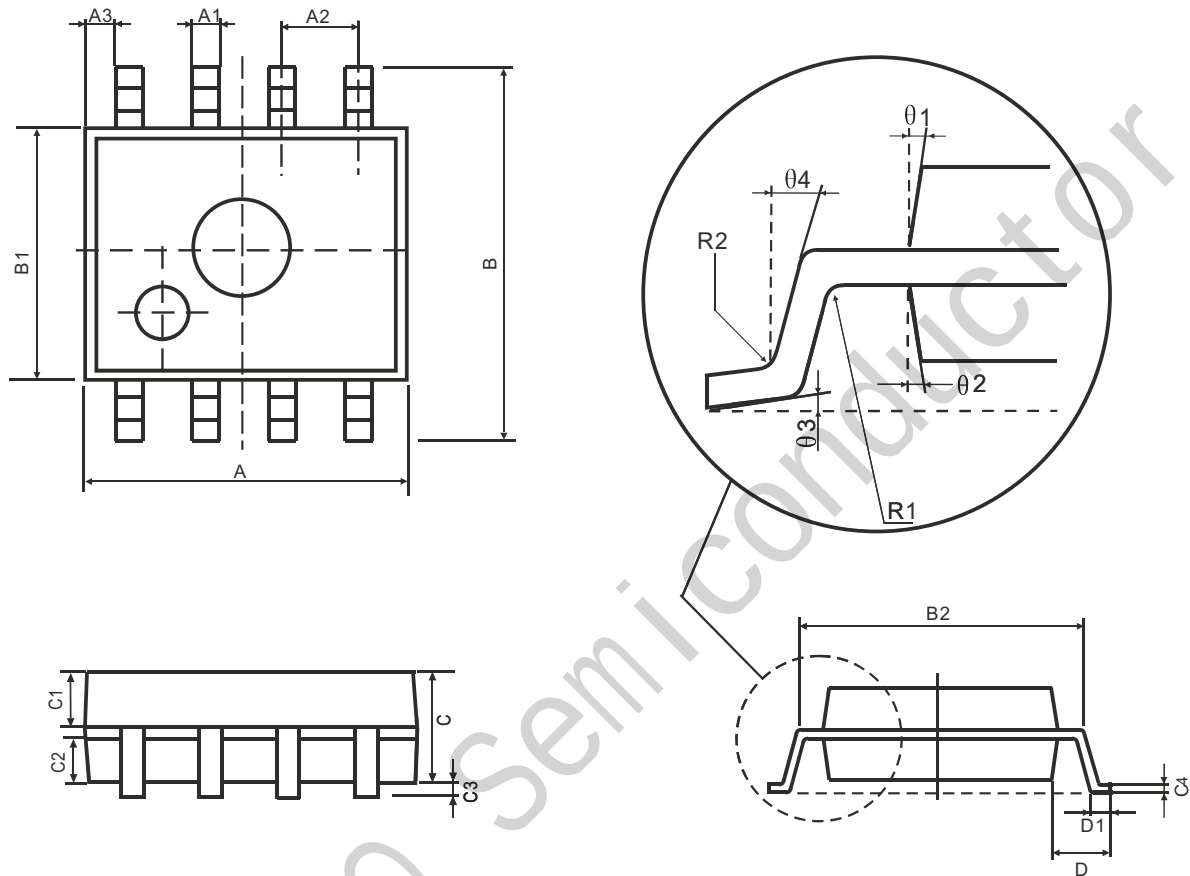


Fig.8 Gate Charge Waveform

外形尺寸图 / Package Dimensions

SOP-8

Dimensions in mm



符号	尺寸(mm)		符号	尺寸(mm)	
	最小值	最大值		最小值	最大值
A	4.95	5.15	C3	0.05	0.20
A1	0.37	0.47	C4	0.20(典型值)	
A2	1.27(典型值)		D	1.05(典型值)	
A3	0.41(典型值)		D1	0.40	0.60
B	5.80	6.20	R1	0.07(典型值)	
B1	3.80	4.00	R2	0.07(典型值)	
B2	5.0(典型值)		θ1	17°(典型值)	
C	1.30	1.50	θ2	13°(典型值)	
C1	0.55	0.65	θ3	4°(典型值)	
C2	0.55	0.65	θ4	12°(典型值)	